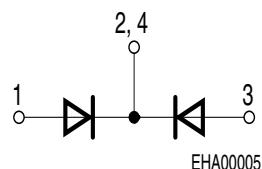
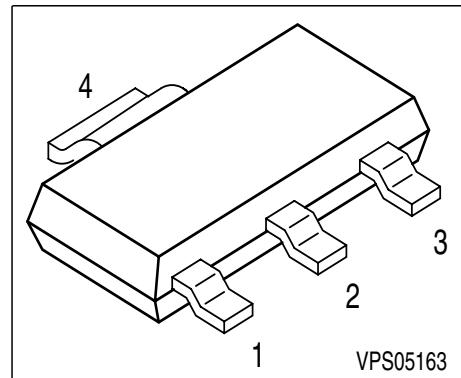


## Silicon Switching Diodes

- Switching applications
- High breakdown voltage
- Common cathode



Type	Marking	Pin Configuration				Package
BAS 79A	BAS 79A	1 = A1	2=C1/2	3 = A2	4=C1/2	SOT-223
BAS 79B	BAS 79B	1 = A1	2=C1/2	3 = A2	4=C1/2	SOT-223
BAS 79C	BAS 79C	1 = A1	2=C1/2	3 = A2	4=C1/2	SOT-223
BAS 79D	BAS 79D	1 = A1	2=C1/2	3 = A2	4=C1/2	SOT-223

## Maximum Ratings

Parameter	Symbol	BAS 79 A	BAS 79 B	BAS 79 C	BAS 79D	Unit
Diode reverse voltage	$V_R$	50	100	200	400	V
Peak reverse voltage	$V_{RM}$	50	100	200	400	
Forward current	$I_F$		1			A
Peak forward current	$I_{FM}$		1			
Surge forward current, $t = 1 \mu s$	$I_{FS}$		10			
Total power dissipation, $T_S = 114^\circ C$	$P_{tot}$		1.2			W
Junction temperature	$T_j$		150			$^\circ C$
Storage temperature	$T_{stg}$		-65 ... 150			

## Thermal Resistance

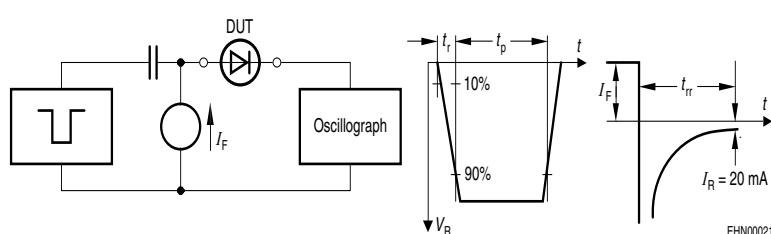
Junction - ambient <sup>1)</sup>	$R_{thJA}$	$\leq 170$	K/W
Junction - soldering point	$R_{thJS}$	$\leq 30$	

1) Package mounted on epoxy pcb 40mm x 40mm x 1.5mm / 6cm<sup>2</sup> Cu

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Breakdown voltage $I_{(\text{BR})} = 100 \mu\text{A}$	$V_{(\text{BR})}$	50	-	-	V
	<b>BAS 79A</b>	100	-	-	
	<b>BAS 79B</b>	200	-	-	
	<b>BAS 79C</b>	400	-	-	
	<b>BAS 79D</b>				
Forward voltage $I_F = 1 \text{ A}$ $I_F = 2 \text{ A}$	$V_F$	-	-	1.6	
Reverse current $V_R = V_{R\text{max}}$	$I_R$	-	-	1	$\mu\text{A}$
Reverse current $V_R = V_{R\text{max}}, T_A = 150^\circ\text{C}$	$I_R$	-	-	50	
<b>AC characteristics</b>					
Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	$C_D$	-	10	-	pF
Reverse recovery time $I_F = 200 \text{ mA}, I_R = 200 \text{ mA}, R_L = 100 \Omega$ , measured at $I_R = 200 \text{ mA}$	$t_{rr}$	-	1	-	$\mu\text{s}$

### Test circuit for reverse recovery time

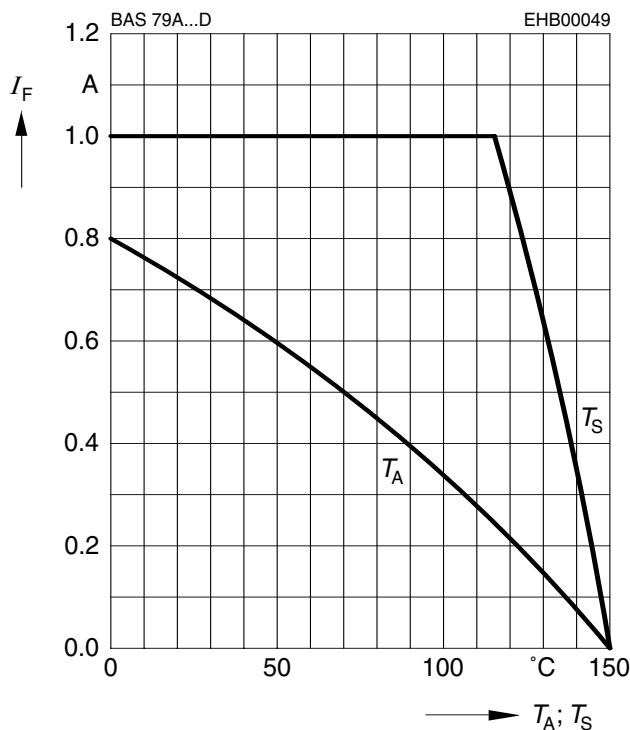


Pulse generator:  $t_p = 100\text{ns}$ ,  $D = 0.05$ ,  
 $t_r = 0.6\text{ns}$ ,  $R_i = 50\Omega$

Oscillograph:  $R = 50\Omega$ ,  $t_r = 0.35\text{ns}$ ,  
 $C \leq 1\text{pF}$

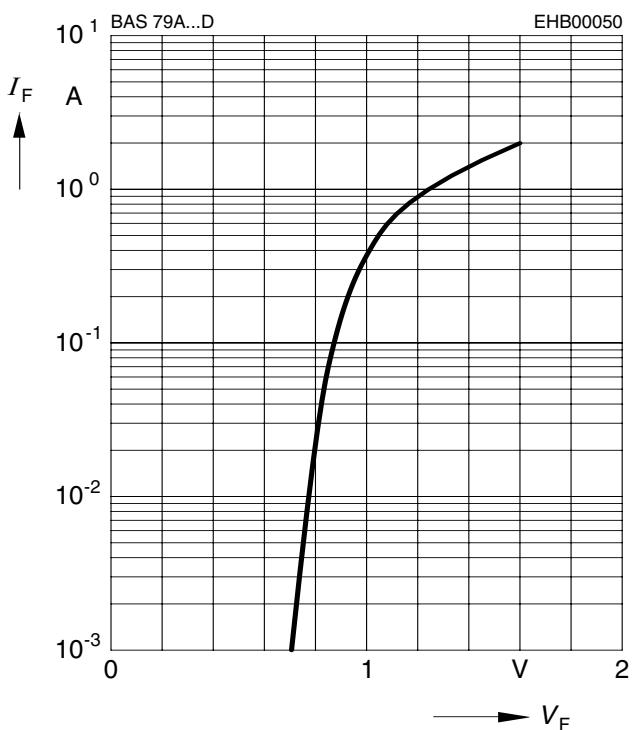
**Forward current  $I_F = f(T_A^*; T_S)$**

\* Package mounted on epoxy



**Forward current  $I_F = f(V_F)$**

$T_A = 25^{\circ}\text{C}$



**Reverse current  $I_R = f(T_A)$**

$V_R = V_{R\max}$

